

# Integrated WOZ Machine (IWM)

## Device Specification

### Features

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- \* Backwards-compatible with 16 sector Disk II controller
- \* Use of 7M (or 8 MHz) to minimize sampling error rate
- \* Fast mode using 2 uS bit cells
- \* Asynchronous mode with pollable handshake registers

### General Description

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The IWM is an integration of the Disk II floppy disc interface. When the IWM is reset, it becomes a controller compatible with the current Disk II interface in its operation with currently supported Apple II and -/// software. In addition the IWM has extensions including a status register, mode register, and mutiple modes of operation. The IWM provides an asynchronous mode which relaxes the precise software/hardware timing required in synchronous mode, a fast mode with a data rate twice that of Disk II, and an optional 1 second one-shot timer to hold the enable outputs low.

The IWM is a peripheral device that connects to a host data bus. ~~It~~ <sup>the</sup> ~~generates and receives serial data.~~ A programmable digital one shot <sup>device</sup> is used <sup>generates</sup> for <sup>and</sup> serial data <sup>recovery</sup>. The IWM generates buffered drive enables and phase line control outputs.

### Packaging and Pin Assignment

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The IWM is packaged in a standard 28 pin, 600 mil plastic DIP .

PHASE0	1	28	PHASE1
PHASE2	2	27	PHASE3
A0	3	26	Vcc
A1	4	25	Q3
A2	5	24	FCLK
A3	6	23	/RESET
/DEV	7	22	RDDATA
WRDATA	8	21	SENSE
/WRREQ	9	20	/ENBL1
D0	10	19	/ENBL2
D1	11	18	D7
D2	12	17	D6
D3	13	16	D5
GND	14	15	D4

Technical Description  
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The primary purpose of the IWM is to allow a microprocessor to read and write serial ~~data from the external data~~. The IWM may be controlled by setting state bits and reading or writing registers. Setting a state bit and accessing a register is done simultaneously. The registers are the mode register, the status register, the write-handshake register, the read data register, and the write data register. ~~These registers are located in the mode register in the IWM and are accessible through the IWM.~~

*Don't*

The data format is an 8 bit nibble with the MSB set. The MSB of the 8 bit data nibble is shifted in or written out first. A bit is transferred every bit cell time. The bit cell time defaults to 4 uS (set to 2 uS in fast mode). Therefore the data rate is one nibble every 32 uS (16 uS in fast mode). ~~When writing data out, the bit cell time is 4 uS in fast mode and 8 uS in slow mode.~~

The IWM is put into the write state by a transition from the write protect sense state to the write load state. In the synchronous mode, the time of that transition and every 8 Q3 periods (4 uS) thereafter, until L7 is cleared, marks the beginning of a write window. The duration of the write window is  $\frac{1}{2}$  periods of the Q3 input signal (2 uS). The the data written at the last write access occurring within this write window will load the shift register with the data to be shifted out. If the next write access has not occurred 32 uS (64 Q3 periods) after a load, the write will be extended in multiples of 4 uS (8 Q3 periods) until another write access, and zeros will be shifted out.

~~which would then be 64 and 80 of the Q3 clock input periods in duration, respectively, and the bit cell timings, 8 Q3 periods per bit cell time in slow mode.~~

~~The~~ The buffer register may be written at any time during the write state. Only the data last written into the buffer register, before the contents of the buffer register is transferred to the write shift register, is used.

In asynchronous mode CLK is used to generate the bit cell timings. In fast mode the CLK clock is equivalent to the clock input on FCLK. In slow mode CLK is equivalent to the clock input on FCLK divided by two. Therefore, in 7M and slow mode the bit cell time will be 28 FCLK clock input periods in duration, in 8M and slow mode the cell time will be 32 periods, and in 8M and fast mode the cell time will be 16 periods. In asynchronous mode the write shift register is loaded every 8 bit cell times starting seven CLK periods after the write state begins.

An underrun occurs when data has not been written to the buffer register between the time the write-handshake bit indicates an empty buffer and the time the buffer is transferred to the write shift-register. If an underrun occurs in asynchronous mode /WRREQ will be disabled (set to a TTL high state) and the /underrun flag will be set to zero. This occurrence can be detected by reading the write-handshake register before clearing state bit L7. Clearing state bit L7 will reset the /underrun flag.

When L6 and L7 are both zero the IWM is in the read state. When reading serial data, a falling transition within a bit cell window is considered to be a one, and no falling transition within a bit cell window is considered to be a zero. The receive data input on RDDATA is synchronized internally with the CLK clock. The synchronized falling transition is then discriminated to the nearest bit cell window using the 7/8 MHz FCLK clock signal in fast mode and the FCLK signal divided by two in slow mode. A digital one-shot data recovery scheme is used. Every falling transition establishes the bit cell windows, used by the data separator in the IWM to recover the following bits, until another falling transition is received.

In the read state the data is shifted into the LSB of the shift register, and the shift register shifts data from LSB to MSB. A full data nibble is considered to be shifted in when a one is shifted into the MSB. When a full data nibble is shifted into the internal shift register, the data will be latched by the read data register and the shift register will be cleared to all zeros so that it will then be ready to shift in the next data word.

In the synchronous mode the shift register is readable in any intermediate state with this exception: when a one is shifted into the MSB, the shift register will appear, to the data bus, to be stalled for a period of two bit times plus four CLK periods. This is to allow the host processor time to poll the MSB to determine when data is valid. In asynchronous mode the data register will latch the shift register when a one is shifted into the MSB and will be cleared 14 FCLK periods (about 2 uS) after a valid data read takes place (a valid data read being defined as both /DEV being low and D7 (the msb) outputting a one from the data register for at least one FCLK period).



## Signal and Bus operation Description

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1. Vcc +5 volt supply  
GND Ground reference and negative supply
2. Device Control Signals
  - A1-A3 These three inputs select one of the 8 bits in the state register to be updated.
  - A0 The data input to the state bit selected by A1-A3. The state to which the addressed state bit is set by an operation will select the register to be accessed by that operation.  
  
Also the /READ input. A low on this input enables the IWM to send the register selected by the state onto the data bus.
  - D0-D7 The bidirectional data bus .
  - /DEV Active low device enable. The falling edge of /DEV latches information on A0-A3. The rising edge of the logical function ( Q3 OR /DEV ) qualifies write register data.
  - FCLK Clock input for the serial data logic; either 7 or 8 MHz.
  - Q3 2.0 Mhz clock input used to qualify the timing of the serial data being written out in the synchronous mode.
  - /RESET Active low system reset input. When asserted, this signal places all IWM outputs in their inactive state, and sets the state and the modes to their defaults.
3. Inputs (2)
  - RDDATA The serial data input. The falling transition of each pulse is synchronized by the IWM.
  - SENSE An input to the IWM that can be polled via the status register.

4. Outputs (8)

WRDATA

The serial data output. A transition occurs on this output for each one bit.

/ENBL1 , /ENBL2

Programmable buffered output lines.

No more than one enable may be low at any time. If an enable is low than Motor-On is true.

If the 1-second on board timer is enabled then the selected one will stay low for about 1 second after it is programmed high.

/WRREQ

This signal is a programmable buffered output line.

PHASE0-3

These are programmable output lines.

A true TTL logic "1" (2.4 volts) can be maintained even while driving two darlington inputs in parallel.

## Register Description

### State Register

This is an 8-bit write-only pseudo-register. The bits in this register are individually addressed by A3,A2,A1. The data on A0 is latched into the addressed state bit by /DEV low. All eight state bits are reset to 0 by /RESET low.

Not only do the state bits control certain chip functions and outputs, the setting of two of the state bits L6 and L7, and Motor-On, internally select which register is to be selected and whether the operation is to be a read or a write. If an operation occurs that changes the state of one of these bits to a new state, that new state will select the register to be accessed during that operation and whether that operation is to be a read or a write.

Address	Name	Function
0		A 1 in this bit will drive PHASE0 to a high state.
1		PHASE1
2		PHASE2
3		PHASE3
4	LMotor-On	A 1 on LMotor-On sets the enable selected below low
5	Drive-Sel	A 1 on this bit selects /ENBL2; a 0 selects /ENBL1
6	L6	(see description below)
7	L7	(see description below)

The state bits L7 and L6, and Motor-On, select which register is available to be read or written. Other registers are read during any operation in which A0 is a zero. A register is written when both L6 and L7 are set or are being set to 1 and A0 is a one.

The combination of L7 and Motor-On and /underrun enables /WRREQ low.

L7	L6	Motor-On	register operation selected	State Name
0	0	0	read all ones	
0	0	1	read data register	Read
0	1	x	read status register	Write-Protect Sense
1	0	x	read write-handshake register	Write
1	1	0	write mode register	Mode Set
1	1	1	write data register	Write Load

Mode register

( a write only register )

All eight mode bits are reset to 0 by /RESET low.

bit	function
LSB 0	1 = latch mode (should be set in asynchronous mode)
1	0 = synchronous handshake protocol; 1 = asynchronous
2	0 = 1-second on board timer enable; 1 = timer disable
3	0 = slow mode; 1 = fast mode ( 2 uS bit cell timing )
4	0 = 7MHz; 1 = 8MHz ( 7 or 8 mHz clock descriptor)
5	1 = test mode; 0 = normal operation
6	1 = MZ-reset
MSB 7	reserved for future expansion

In latch mode the msb of the read data is latched internally during /DEV low (this internally latched msb is then used for the determination of a valid data read).

If the 1-second timer bit is a zero then the enable (/ENBL1 or /ENBL2) selected by Drive-Sel will be held low for  $2^{23} \pm 100$  FCLK periods (about 1 second) after the LMOTOR-ON state bit is reset to zero. If the latch mode bit is set the timer is not guaranteed to count up to  $2^{23}$ . MOTOR-ON is synonymous with either /ENBL1 or /ENBL2 being low.

Fast mode selects a bit cell time of 2 uS instead of 4 uS. The 7/8 mHz descriptor indicates whether the input clock (FCLK) is to be divided by 7 or 8 to provide 1 uS internal timings.

When the test mode bit is a 1, device operation is unspecified, except that status register bit 5 can always be read and that the mode register can always be set.

Status register ( a read-only register )

<u>bit</u>	<u>function</u>
0-4	same as mode register
5	1 = either /ENBL1 or /ENBL2 is currently active (low)
6	1 = MZ ( reset to 0 by /RESET and MZ-reset )
7	1 = SENSE input high; 0 = SENSE input low

The MZ bit is reserved for compatibility with future products and should always be read as a zero.

Handshake Register ( a read only register )

<u>bit</u>	<u>function</u>
0-5	reserved for future use (currently read as ones)
6	1 = write state ( cleared to 0 if a write underrun occurs )
7	1 = write data buffer register ready for data

Data Register

The operation of the data register depends on the setting of state bits L6 and L7 and on the synchronous mode bit. With L6 and L7 clear, the data register operates as a read data register. With L7 set the data register operates in the write state as a write data buffer.

## Maximum Ratings

supply voltage	-0.3 to +7.0 V
input voltage	-0.3 to +7.0 V
storage temperature	-35 to +125 degrees C
operating temperature	0 to +70 degrees C (ambient)

## DC characteristics

sym	parameter	min	max	units	notes
Vcc	supply voltage	4.75	5.25	Volts	
Icc	supply current	—	200	mA	5
Vil	Input low	—	0.8	V	3
Vih	Input high	2.0	—	V	4
Ii	input leakage	—	100	uA	1
Vol	TTL output low	—	.4	V	—
Voh	TTL output high	2.4	—	V	—
Ioh	source current at Voh	.32	—	mA	2
Iol	sink current at Vol	3.2	—	mA	2

## Notes

### 1. Inputs.

The inputs have static protection. All IWM inputs and bidirectional lines in the input mode are high impedance except as noted below:

WPROT and /RDDATA : pullup to VCC of 10K ohms nominal  
(source current of 80 to 600 uA at 0.4 to 2.8 Volts)

### 2. Outputs Ioh and Iol apply to D0 thru D7 and WRDATA. The following output lines have special drive capabilities, noted below.

/ENBL1, /ENBL2: Sink current of at least 5.0 mA at Vol  
Source current of at least 40 uA at Voh  
/WRREQ: Sink current of at least 10.0 mA at Vol  
Source current of at least 40 uA at Voh

PHASE0-3: Source current of at least 1.0 mA at Voh  
Source current of 0.5 mA when pulled down to 3.0 V.  
Sink current of at least 2.4 mA at Vol

3. TTL Vil is also referred to as a zero.

4. TTL Vih is also referred to as a one.

5. at 5.25 V over full operating temperature range.

## AC characteristics

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sym	parameter	min	max	units	notes
tas	A0-A3 to /DEV, fe	40	—	nS	setup
tah	/DEV, re to A0-A3 invalid	-1	—	nS	addr hold
tds	data to (Q3 OR /DEV), re	50	—	nS	setup
tdh	(Q3 OR /DEV), re to data	10	—	nS	data hold
tda	/DEV, fe to data out	—	200	nS	access, 1.
tdsl	/DEV low	200	—	nS	6.
tdsh	/DEV high	450	—	nS	
tde	/DEV to /ENBLx or /WRREQ	—	500	nS	2.
tdph	/DEV to PHASEx	—	500	nS	2.
trdh	RDDATA high time	300	—	nS	5.
tckh	FCLK high time	50	200	nS	
tckl	FCLK low time	50	200	nS	
tckp	FCLK period	120	143	nS	
tckpt	FCLK period, no timer	120	500	nS	11.
tqds1	Q3, re to /DEV, fe	1	100	nS	7.
tqds2	Q3, re to /DEV, re	1	100	nS	7.
tq3h	Q3 high	260	300	nS	7.
tq3l	Q3 low	190	—	nS	7.
tdmsbh	D0-6 valid to D7 re	50	—	nS	8.
tres	/RESET low time	500	—	nS	10.
trwrh	/RESET to /WRREQ high	—	300	nS	
tsj	sampling jitter	—	12.5	nS	4.
tckwr	write clock, re to WRDATA	—	500	nS	9.
twrj	write data jitter	—	62.5	nS	9.
cp	pin capacitance	—	15	pF	

## notes

1. Load = 130 pF and 8 LS TTL loads
2. Load = 100 pf and rated maximum current
3. fe = falling edge ( TTL high to low )  
re = rising edge
4. tsj is the uncertainty window in sampling the asynchronous input RDDATA and synchronizing it internally with CLK at any constant Vcc and temperature.
5. trdh and trdl must be at least twice the period of CLK to be properly synchronized.
6. the time between 2 successive /DEV selects will be greater than 2 CLK periods, and in synchronous mode will be no less than 1 Q3 period.  
/DEV may be held low indefinitely.
7. These apply to the synchronous mode only. In other modes Q3 may be held low indefinitely.
8. If, when /DEV is low, data on D0-7 is changing to a word with D7 high, the data on D0-6 must become valid before the rising edge of D7 .
9. tckwr is the time from FCLK, re, in asynchronous mode, or Q3, re, in synchronous mode, to changes in the output WRDATA, driving a load of 100 pF.  
twrj is the change in tckwr from edge to edge of WRDATA at any constant Vcc and temperature.
10. for test purposes tres must be at least 24 times tckp .
11. tckpt is max FCLK period with 1-second timer disabled.

This specification is confidential to Apple and contains proprietary information.

changes from earlier specs

A0-3 pinout corrected  
/ENBL1 and /ENBL2 pinout corrected  
tdmsbh specified  
latch mode added (change to breadboard also)

changes from rev#11 spec (4/16/82)

D0-7 pinout changed to facilitate IC layout  
write jitter specified

changes from rev#12 spec (5/5/82)

Address setup time changed to 40 nS

changes from rev#14 spec (6/4/82)

LMotor-On different from Motor-On  
Phase lines sink 2.4 mA  
tres test condition added  
underrun and other nomenclature cleared up

changes from rev#17 spec (8/17/82)

read data stall time changed to 4 CLKs  
relaxed AC and DC characteristics

rhn 02/05/82  
bcs 01/11/82  
ws 10/20/81  
woz 1978,79

4. Outputs (8)

WRDATA

The serial data output. A transition occurs on this output for each one bit.

/ENBL1 , /ENBL2

Programmable buffered output lines. No more than one enable may be low at any time. If an enable is low than Motor-On is true. If the 1-second on board timer is enabled then the selected one will stay low for about 1 second after it is programmed high.

/WRREQ

This signal is a programmable buffered output line.

PHASE0-3

These are programmable output lines. A true TTL logic "1" (2.4 volts) can be maintained even while driving two darlington inputs in parallel.

## Register Description

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### State Register

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This is an 8-bit write-only pseudo-register. The bits in this register are individually addressed by A3,A2,A1. The data on A0 is latched into the addressed state bit by /DEV low. All eight state bits are reset to 0 by /RESET low.

Not only do the state bits control certain chip functions and outputs, the setting of two of the state bits L6 and L7, and Motor-On, internally select which register is to be selected and whether the operation is to be a read or a write. If an operation occurs that changes the state of one of these bits to a new state, that new state will select the register to be accessed during that operation and whether that operation is to be a read or a write.

Address	Name	Function
0		A 1 in this bit will drive PHASE0 to a high state.
1		PHASE1
2		PHASE2
3		PHASE3
4	LMotor-On	A 1 on LMotor-On sets the enable selected below low
5	Drive-Sel	A 1 on this bit selects /ENBL2; a 0 selects /ENBL1
6	L6	(see description below)
7	L7	(see description below)

The state bits L7 and L6, and Motor-On, select which register is available to be read or written. Other registers are read during any operation in which A0 is a zero. A register is written when both L6 and L7 are set or are being set to 1 and A0 is a one.

The combination of L7 and Motor-On and /underrun enables /WRREQ low.

L7	L6	Motor-On	register operation selected	State Name
0	0	0	read all ones	
0	0	1	read data register	Read
0	1	x	read status register	Write-Protect Sense
1	0	x	read write-handshake register	Write
1	1	0	write mode register	Mode Set
1	1	1	write data register	Write Load

Mode register ( a write only register )

All eight mode bits are reset to 0 by /RESET low.

bit	function
LSB 0	1 = latch mode (should be set in asynchronous mode)
1	0 = synchronous handshake protocol; 1 = asynchronous
2	0 = 1-second on board timer enable; 1 = timer disable
3	0 = slow mode; 1 = fast mode ( 2 uS bit cell timing )
4	0 = 7MHz; 1 = 8MHz ( 7 or 8 mHz clock descriptor)
5	1 = test mode; 0 = normal operation
6	1 = MZ-reset
MSB 7	reserved for future expansion

In latch mode the msb of the read data is latched internally during /DEV low (this internally latched msb is then used for the determination of a valid data read).

If the 1-second timer bit is a zero then the enable (/ENBL1 or /ENBL2) selected by Drive-Sel will be held low for  $2^{23} + 100$  FCLK periods (about 1 second) after the LMOTOR-ON state bit is reset to zero. If the latch mode bit is set the timer is not guaranteed to count up to  $2^{23}$ . MOTOR-ON is synonymous with either /ENBL1 or /ENBL2 being low.

Fast mode selects a bit cell time of 2 uS instead of 4 uS. The 7/8 mHz descriptor indicates whether the input clock (FCLK) is to be divided by 7 or 8 to provide 1 uS internal timings.

When the test mode bit is a 1, device operation is unspecified, except that status register bit 5 can always be read and that the mode register can always be set.

Status register ( a read-only register )

<u>bit</u>	<u>function</u>
0-4	same as mode register
5	1 = either /ENBL1 or /ENBL2 is currently active (low)
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7	1 = SENSE input high; 0 = SENSE input low

The MZ bit is reserved for compatibility with future products and should always be read as a zero.

Handshake Register ( a read only register )

<u>bit</u>	<u>function</u>
0-5	reserved for future use (currently read as ones)
6	1 = write state ( cleared to 0 if a write underrun occurs )
7	1 = write data buffer register ready for data

Data Register

The operation of the data register depends on the setting of state bits L6 and L7 and on the synchronous mode bit. With L6 and L7 clear, the data register operates as a read data register. With L7 set the data register operates in the write state as a write data buffer.

## Maximum Ratings

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storage temperature	-35 to +125 degrees C
operating temperature	0 to +70 degrees C (ambient)

## DC characteristics

sym	parameter	min	max	units	notes
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Icc	supply current	—	200	mA	5
Vil	Input low	—	0.8	V	3
Vih	Input high	2.0	—	V	4
Ii	input leakage	—	100	uA	1
Vol	TTL output low	—	.4	V	
Voh	TTL output high	2.4	—	V	
Ioh	source current at Voh	.32	—	mA	2
Iol	sink current at Vol	3.2	—	mA	2

## Notes

### 1. Inputs.

The inputs have static protection. All IWM inputs and bidirectional lines in the input mode are high impedance except as noted below:

WPROT and /RDDATA : pullup to VCC of 10K ohms nominal  
(source current of 80 to 600 uA at 0.4 to 2.8 Volts)

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Source current of 0.5 mA when pulled down to 3.0 V.  
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tdh	(Q3 OR /DEV), re to data	10	—	nS	data hold
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tres	/RESET low time	500	—	nS	10.
trwrh	/RESET to /WRREQ high	—	300	nS	
tsj	sampling jitter	—	12.5	nS	4.
tckwr	write clock, re to WRDATA	—	500	nS	9.
twrj	write data jitter	—	62.5	nS	9.
cp	pin capacitance	—	15	pF	

## notes

1. Load = 130 pF and 8 LS TTL loads
2. Load = 100 pf and rated maximum current
3. fe = falling edge ( TTL high to low )  
re = rising edge
4. tsj is the uncertainty window in sampling the asynchronous input RDDATA and synchronizing it internally with CLK at any constant Vcc and temperature.
5. trdh and trdl must be at least twice the period of CLK to be properly synchronized.
6. the time between 2 successive /DEV selects will be greater than 2 CLK periods, and in synchronous mode will be no less than 1 Q3 period.  
/DEV may be held low indefinitely.
7. These apply to the synchronous mode only. In other modes Q3 may be held low indefinitely.
8. If, when /DEV is low, data on D0-7 is changing to a word with D7 high, the data on D0-6 must become valid before the rising edge of D7 .
9. tckwr is the time from FCLK, re, in asynchronous mode, or Q3, re, in synchronous mode, to changes in the output WRDATA, driving a load of 100 pF.  
twrj is the change in tckwr from edge to edge of WRDATA at any constant Vcc and temperature.
10. for test purposes tres must be at least 24 times tckp .
11. tckpt is max FCLK period with 1-second timer disabled.

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Phase lines sink 2.4 mA  
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